

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTP180N085T

RDS(• Fully ch • 100% a • Minimu	drain-source on-resistance: on) $\leq 5.5 m \Omega @V_{GS} = 10V$ haracterized avalanche voltage and of avalanche tested im Lot-to-Lot variations for robust dev hance and reliable operation			pin 1, Gate 1 2 3 1 2 2 1 2 2 1 2 3 2, Drain 3, Source TO-220C package
• DC/DC	Converters			
-	urrent Switching Applications _UTE MAXIMUM RATINGS(T _a =25°C			
SYMBOL	PARAMETER	VALUE	UNIT	↓
V _{DSS}	Drain-Source Voltage	85	V	
V _{GS}	Gate-Source Voltage	±20	V	↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓
Ι _D	Drain Current-Continuous	180	Α	
I _{DM}	Drain Current-Single Pulsed	480	A	↑ mm
PD	Total Dissipation @T _C =25℃	430	W	DIM MIN MAX A 15.50 15.90 B 9.90 10.20
Tj	Operating Junction Temperature	-55~175	°C	C 4.20 4.50 D 0.70 0.90 F 3.40 3.70
T _{stg}	Storage Temperature	-55~175	°C	G 4.98 5.18 H 2.68 2.90
• THERM	IAL CHARACTERISTICS			J 0.44 0.60 K 13.00 13.40 L 1.10 1.45

1

SYMBOL	SYMBOL PARAMETER		UNIT			
R _{th(j-c)}	h(j-c) Junction-to-case thermal resistance		°C/W			

Q

R

U

v

2.70

2.30

1.29

6.45 8.66 2.90

2.70

1.35

6.65

8.86



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V; ID = 250 μ A	85		V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} = V _{GS} ; ID = 250 μ A	2.0	4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 25A		5.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V		±200	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V	5		
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 150°C		250	μA
Vsd	Diode forward voltage	I _F = 25A; V _{GS} = 0V		1.0	V

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